

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:
David S. Pecora

Serial No.: 09/854,206

Filed: May 11, 2001

For: **ETCH OF SILICON NITRIDE SELECTIVE TO
SILICON AND SILICON DIOXIDE USEFUL
DURING THE FORMATION OF A
SEMICONDUCTOR DEVICE**



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§ Group Art Unit: 1765
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§ Examiner: Binh X. Tran
§
§ Atty. Docket: 00-0737.00/US
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§ Paper No. 3
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Commissioner for Patents
Washington, D.C. 20231

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July 24, 2002 *John Chelms*
Date Signature

RESPONSE TO THE OFFICE ACTION OF APRIL 24, 2002

Please enter the following in response to the Examiner's outstanding office action mailed April 24, 2002.

In the Claims

Please rewrite the following claims to the form indicated below.

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- Sub B2
A1
1. (amended) A method for etching a layer of silicon nitride comprising:
- etching said silicon nitride layer in the absence of a photoresist layer with an etchant consisting essentially of oxygen at a flow rate of between about 20 sccm and about 80 sccm and one of CHF_3 and CH_2F_2 at a flow rate of between about 5 sccm and about 25 sccm; and
- during said etching, subjecting said silicon nitride layer to a pressure of between about 10 millitorr and about 60 millitorr.